

#### 30V PNP LOW SATURATION MEDIUM POWER TRANSISTOR

#### **Features**

- BV<sub>CEO</sub> > -30V
- I<sub>C</sub> = -5.5A Continuous Collector Current
- I<sub>CM</sub> = -20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(SAT)</sub> < -60mV max @ -1A</li>
- $R_{SAT} = 24m\Omega$  @ -5.5A for Low Equivalent On-Resistance
- Exceptional Gain Linearity Down to -10mA
- hFE Specified up to -20A for High Gain Hold Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

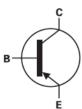
- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
  UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.05 grams (Approximate)

#### **Applications**

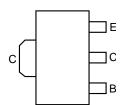
- DC-DC Converters
- MOSFET Gate Drivers
- · Charging Circuits
- Power Switches
- Motor Control







**Device Schematic** 



Pin-Out Top View

#### Ordering Information (Note 4)

Part Number		Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel	
	ZXTP2008ZTA	949	7	12	1.000	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**

949 = Product Type Marking Code



### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-30	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-5.5	Α
Peak Pulse Current	I <sub>CM</sub>	-20	A

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	ם	1.5 12	W	
Linear Derating Factor	(Note 6)	$P_{D}$	2.1 16.8	mW/°C	
Thermal Desistance Junction to Ambient	(Note 5)	$R_{ heta JA}$	83		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	60	°C/W	
Thermal Resistance, Junction to Lead	(Note 7)	$R_{ heta JL}$	3.23		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

# ESD Ratings (Note 8)

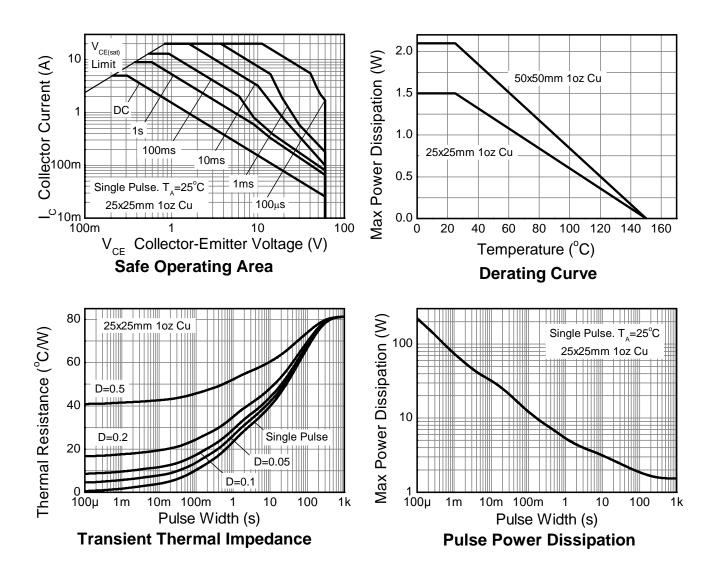
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.
- Same as Note 5, except the device is mounted on 50mm x 50mm 1oz copper.
  Thermal resistance from junction to solder-point (at the end of the collector lead).
  Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





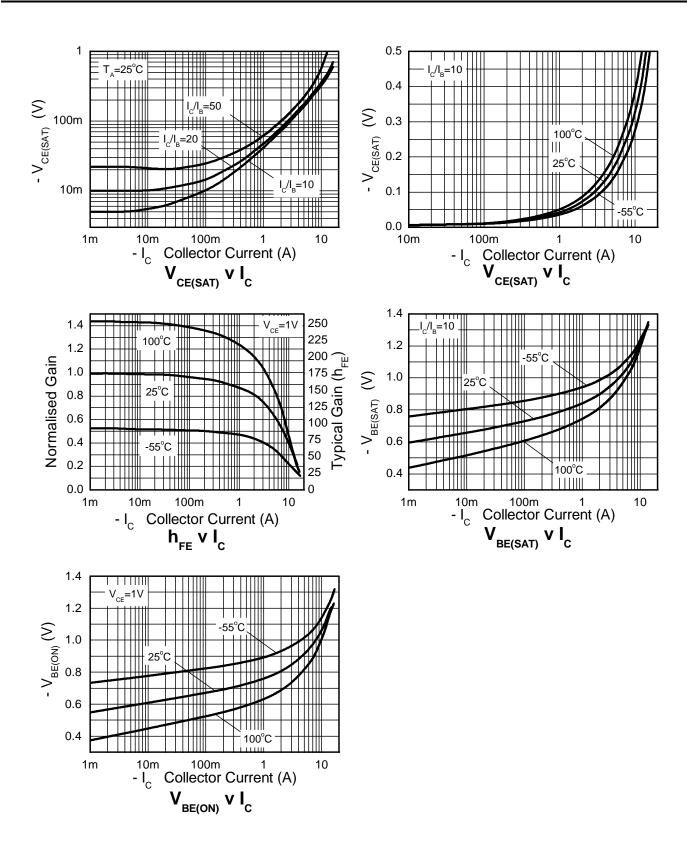
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		-50	-70	_	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage	$BV_{CER}$	-50	-70	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-30	-40	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	lone	_	< -1	-20	nA	V <sub>CB</sub> = -40V
Collector Catori Carrent	Ісво	_	_	-0.5	μΑ	$V_{CB} = -40V, T_A = +100^{\circ}C$
Collector Cutoff Current	lorn	_	< -1	-20	nA	V <sub>CB</sub> = -40V, R≤1kΩ
Collector Guton Gurrent	I <sub>CER</sub>	_	_	-0.5	μΑ	V <sub>CB</sub> = -40V, T <sub>A</sub> = +100°C, R≤1kΩ
Emitter Cutoff Current	I <sub>EBO</sub>		< -1	-10	nA	V <sub>EB</sub> = -6V
			-25	-40		$I_C = -0.5A$ , $I_B = -20mA$
	V <sub>CE</sub> (SAT)		-35	-55		$I_C = -1A$ , $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 9)			-55	-80		$I_C = -1A$ , $I_B = -20mA$
			-55	-80		$I_C = -2A$ , $I_B = -200mA$
			-130	-175		$I_C = -5.5A$ , $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(SAT)</sub>	_	-970	-1070	mV	$I_C = -5.5A$ , $I_B = -500mA$
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(ON)</sub>	_	-860	-960	mV	I <sub>C</sub> = -5.5A, V <sub>CE</sub> = -1V
		100	225			$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
DC Current Gain (Note 9)	L	100	200	300		$I_{C} = -1A$ , $V_{CE} = -1V$
DC Current Gain (Note 9)	hFE	70	145		_	$I_{C} = -5A$ , $V_{CE} = -1V$
		10	20			$I_C = -20A$ , $V_{CE} = -1V$
Transition Frequency	f⊤	_	110		MHz	$V_{CE} = -10V, I_{C} = -100mA,$
Transmort requestey					IVII IZ	f = 50MHz
Output Capacitance (Note 9)	C <sub>OBO</sub>	_	83	_	pF	$V_{CB} = -10V$ , $f = 1MHz$
Switching Times	t <sub>ON</sub>	_	43	_	no	$V_{CC} = -10V, I_{C} = -1A,$
Switching Times	t <sub>OFF</sub>	_	230	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

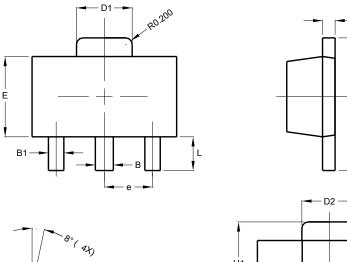




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT89



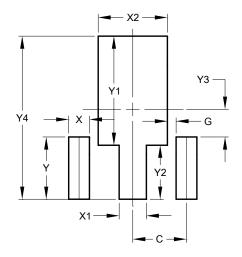
		-	D2 —	-		
•		_		$\neg$		
 H1				11		
	_	_		E2		
<u>,                                     </u>	Lm	$\downarrow$	. Ì _	╛	<b>-</b>	 L1
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SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
Η	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
Z	0.20	0.40	0.30			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT89



Dimensions	Value	
	(in mm)	
С	1.500	
G	0.244	
X	0.580	
X1	0.760	
X2	1.933	
Υ	1.730	
Y1	3.030	
Y2	1.500	
Y3	0.770	
Y4	4.530	



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